

isc Silicon NPN Power Transistor

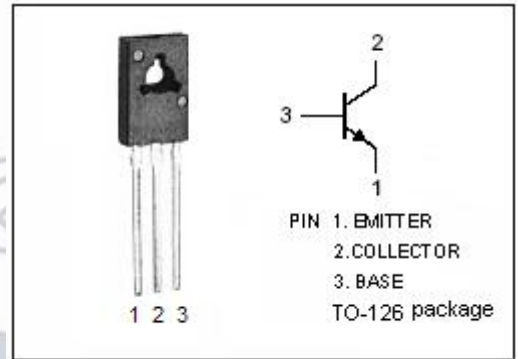
BD189

DESCRIPTION

- DC Current Gain-
: $h_{FE} = 40(\text{Min}) @ I_C = 0.5A$
- Collector-Emitter Sustaining Voltage -
: $V_{CEO(SUS)} = 60V(\text{Min})$
- Complement to type BD190

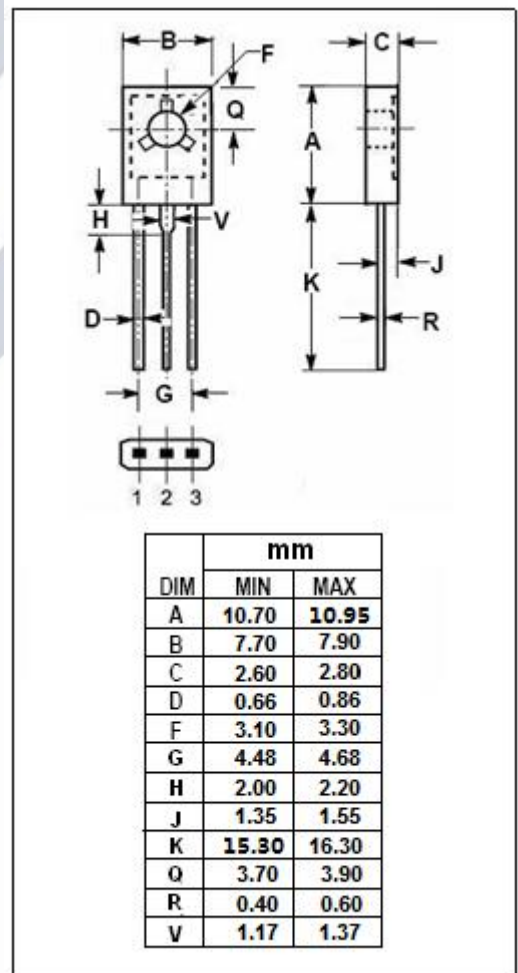
APPLICATIONS

- Designed for use in 5~10 Watt audio amplifiers utilizing Complementary or quasi complementary circuits.



ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	70	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	40	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.12	$^\circ C/W$

isc Silicon NPN Power Transistor**BD189****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=50\text{mA}; I_B=0$	60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.2\text{A}$			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=2\text{A}; V_{CE}=2\text{V}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=70\text{V}; I_E=0$			100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1.0	mA
h_{FE-1}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=2\text{V}$	40			
h_{FE-2}	DC Current Gain	$I_C=2\text{A}; V_{CE}=2\text{V}$	15			
f_T	Current-Gain—Bandwidth Product	$I_C=1\text{A}; V_{CE}=10\text{V}; f=1\text{MHz}$	2.0			MHz